Silicon PNP Power Transistors 2SA715

DESCRIPTION

・With TO-126 package
・Complement to type 2SC1162

APPLICATIONS

・Low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

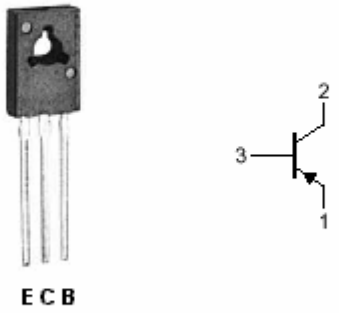

Fig.1 simplified outline (TO-126) and symbol

Absolute Maximun Ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-35	V
V_{CEO}	Collector-emitter voltage	Open base	-35	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-2.5	A
I_{CM}	Collector current-Peak		-3	A
P_C	Collector power dissipation	T_a=25℃	0.75	W
		T_C=25℃	10	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA; R_{BE}=∞	-35			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA ;I_E=0	-35			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-1mA ;I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-2.0A ;I_B=-0.2A(Pulse test)		-0.5	-1.0	V
V_{BE}	Base-emitter voltage	I_C=-1.5A;V_{CE}=-2V(Pulse test)		-1.0	-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-35V; I_E=0			-20	μA
h_{FE-1}	DC current gain	I_C=-0.5A ; V_{CE}=-2V	60		320	
h_{FE-2}	DC current gain	I_C=-1.5A ; V_{CE}=-2V(Pulse test)	20			
f_T	Transition frequency	I_C=-0.2A ; V_{CE}=-2V(Pulse test)		160		MHz

◆ **h_{FE-1} Classifications**

B	C	D
60-120	100-200	160-320

PACKAGE OUTLINE

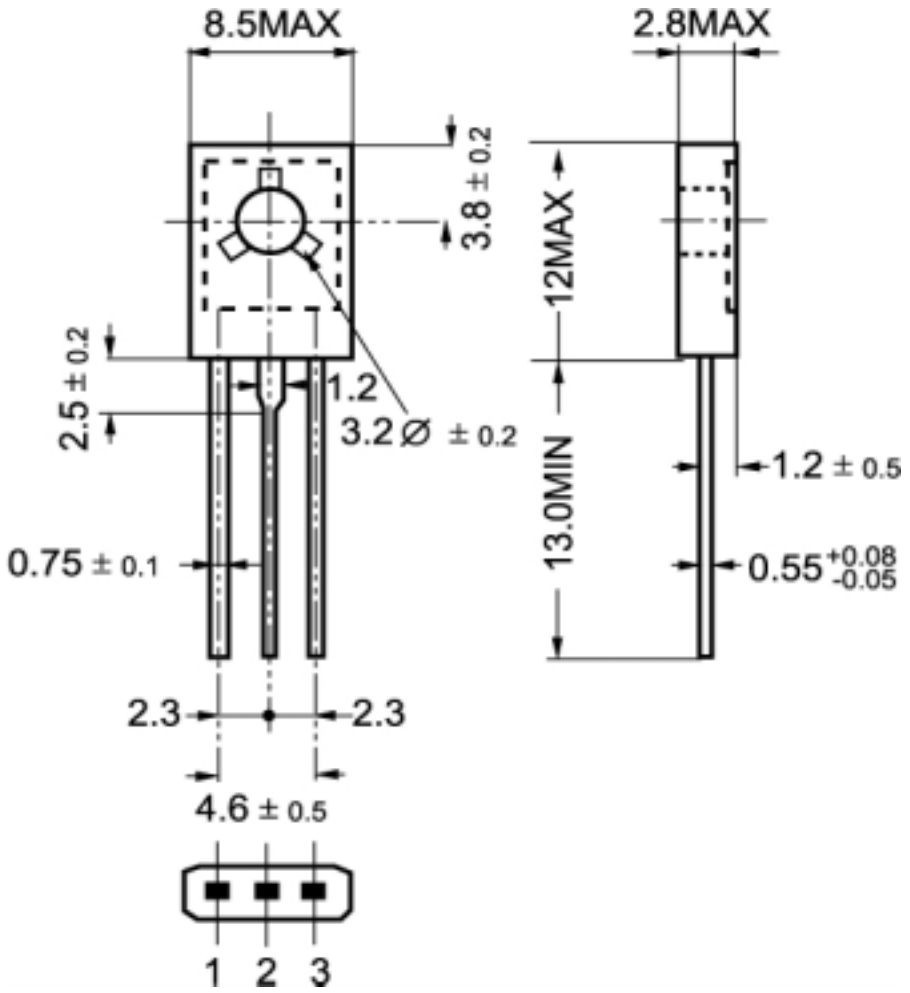

Fig.2 Outline dimensions

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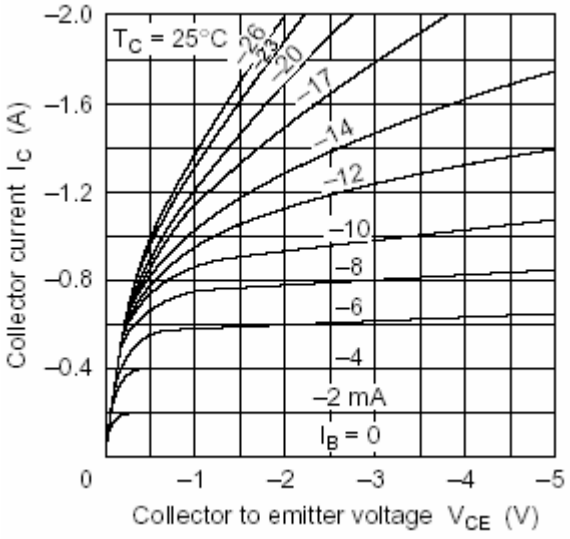

Fig.3 Static Characteristic

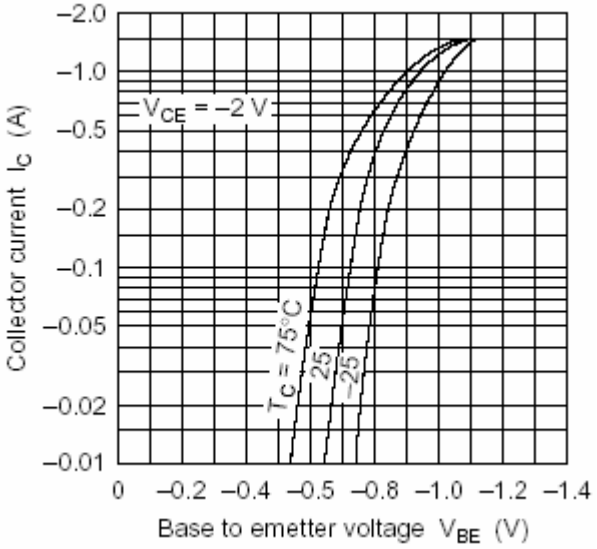

Fig.4 Base-Emitter On Voltage

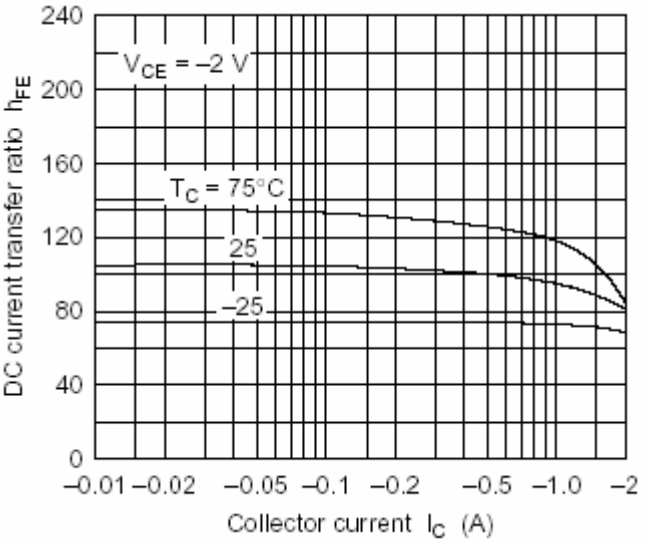

Fig.5 DC current Gain

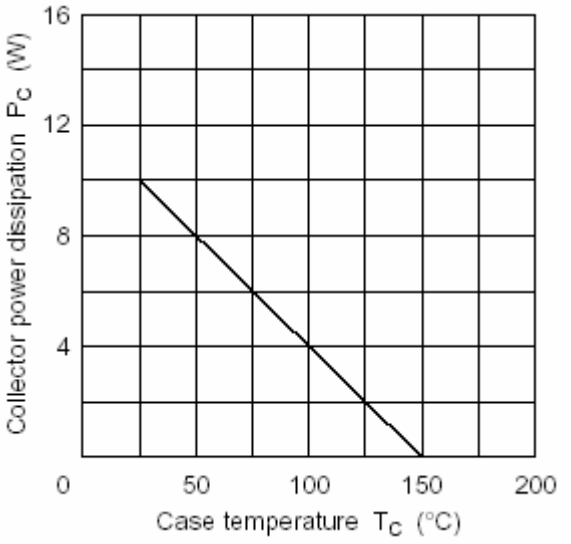

Fig.6 Power Derating

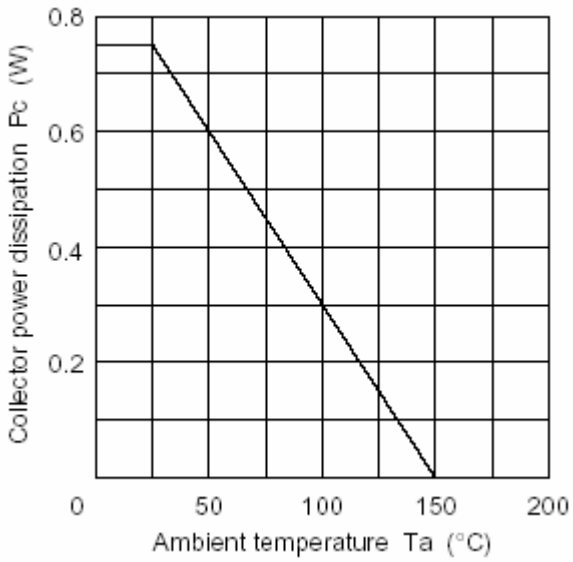

Fig.7 Power Derating

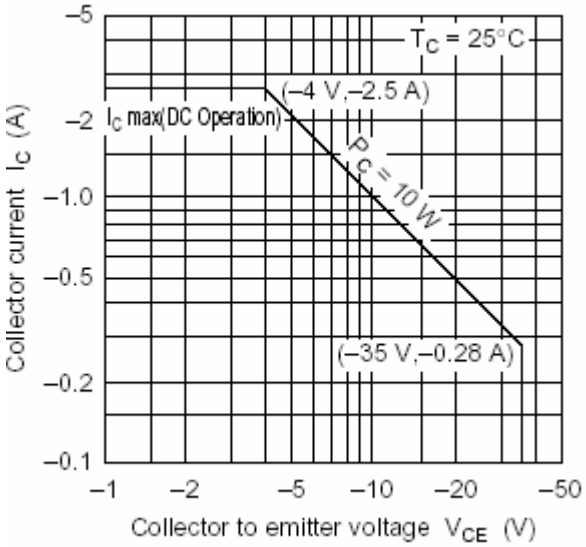

Fig.8 Safe Operating Area